**Product data sheet** 

# 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Logic-level compatible
- Trench MOSFET technology
- Very fast switching
- AEC-Q101 qualified

# 3. Applications

- High-side loadswitch
- High-speed line driver
- Relay driver
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>amb</sub> = 25 °C		-	-	-20	V
V <sub>GS</sub>	gate-source voltage			-12	-	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-	-3.5	Α
Static characte	Static characteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -4.5 V; $I_D$ = -2.4 A; $T_j$ = 25 °C		-	48	55	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

#### Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	<u></u> 3	D I
2	S	source		
3	D	drain	1 2	G TITLE
			TO-236AB (SOT23)	S
				017aaa094

# 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMV48XPA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

# 7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMV48XPA	%DZ

[1] % = placeholder for manufacturing site code

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## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>amb</sub> = 25 °C		-	-20	V
$V_{GS}$	gate-source voltage			-12	12	V
I <sub>D</sub>	drain current	$V_{GS}$ = -4.5 V; $T_{amb}$ = 25 °C	[1]	-	-3.5	Α
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-2.2	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-14	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	<u>[2]</u>	-	510	mW
			[1]	-	930	mW
		T <sub>sp</sub> = 25 °C		-	4150	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-dra	in diode	,			1	
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	-1	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

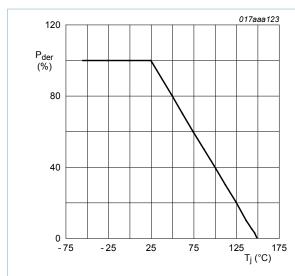


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

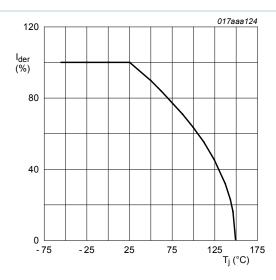


Fig. 2. Normalized continuous drain current as a function of junction temperature

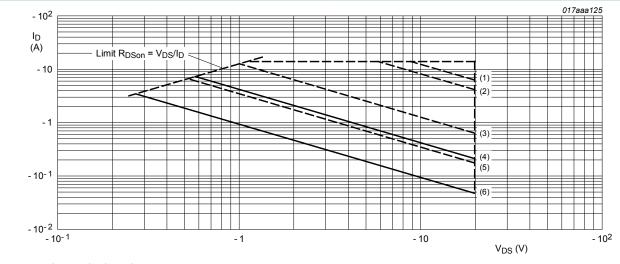
$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

PMV48XPA

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I<sub>DM</sub> = single pulse

(1)  $t_p = 100 \mu s$ 

(2)  $t_p = 1 \text{ ms}$ 

(3)  $t_p = 10 \text{ ms}$ 

(4) DC;  $T_{sp}$  = 25 °C

 $(5) t_p = 100 \text{ ms}$ 

(6) DC;  $T_{amb}$  = 25 °C; drain mounting pad 6 cm<sup>2</sup>

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uity a)	thermal resistance from junction to ambient	in free air	[1]	-	213	245	K/W
			[2]	-	117	135	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	25	30	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

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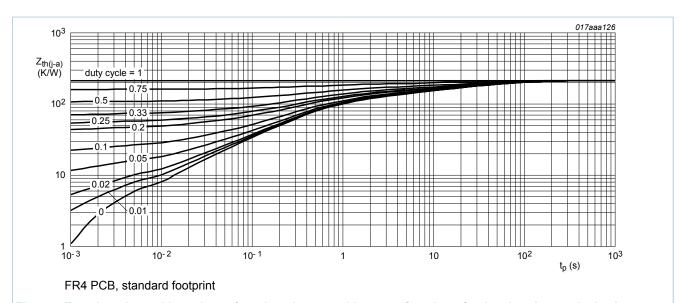


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

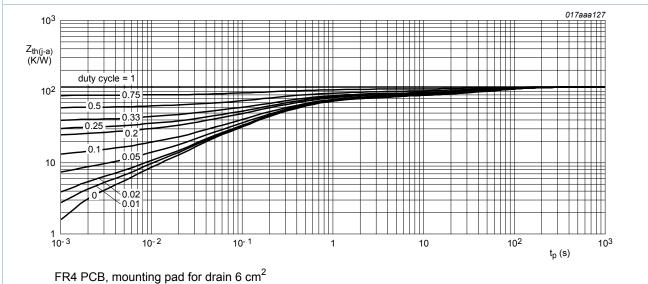


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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## 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		'			
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-0.75	-1	-1.25	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = -20 V; V <sub>GS</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	-1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = -12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = -4.5 V; $I_D$ = -2.4 A; $T_j$ = 25 °C	-	48	55	mΩ
	resistance	$V_{GS}$ = -4.5 V; $I_D$ = -2.4 A; $T_j$ = 150 °C	-	70	80	mΩ
		V <sub>GS</sub> = -2.5 V; I <sub>D</sub> = -2 A; T <sub>j</sub> = 25 °C	-	71	81	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = -12 V; $I_D$ = -2 A; $T_j$ = 25 °C	-	12	-	S
Dynamic cl	naracteristics		'			
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = -10 V; $I_{D}$ = -1 A; $V_{GS}$ = -4.5 V;	-	8.5	11	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	1.8	-	nC
$Q_{GD}$	gate-drain charge		-	1.8	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	1000	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	130	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	90	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -10 V; $I_{D}$ = -1 A; $V_{GS}$ = -4.5 V;	-	11	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega$ ; $T_j = 25 ^{\circ}C$	-	13	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	61	-	ns
t <sub>f</sub>	fall time		-	23	-	ns
Source-dra	in diode	1		1	1	
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = -2.4 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	-0.82	-1.2	V

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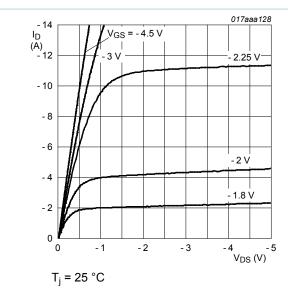
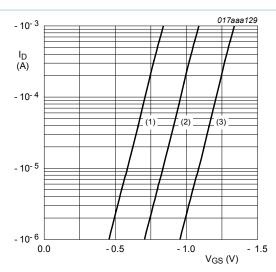


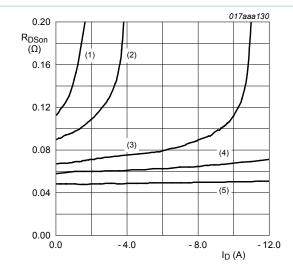
Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



$$T_i = 25 \,^{\circ}\text{C}; \, V_{DS} = -3 \,^{\circ}\text{V}$$

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage



$$T_i = 25 \,^{\circ}C$$

$$(1) V_{GS} = -1.8 V$$

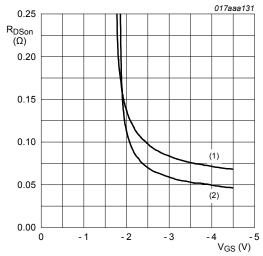
(2) 
$$V_{GS} = -2.0 \text{ V}$$

$$(3) V_{GS} = -2.25 V$$

$$(4) V_{GS} = -3.0 V$$

$$(5) V_{GS} = -4.5 V$$

Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



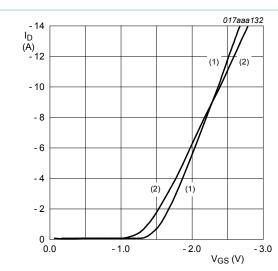
(1) 
$$T_i = 125 \, ^{\circ}C$$

(2) 
$$T_i = 25 \, ^{\circ}C$$

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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$$V_{DS} > I_{D} \times R_{DSon}$$

(1) 
$$T_i = 25 \,^{\circ}C$$

(2) 
$$T_j = 150 \, ^{\circ}\text{C}$$

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

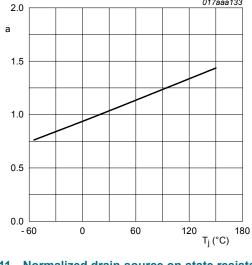
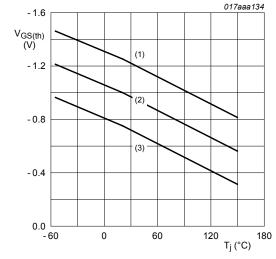


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

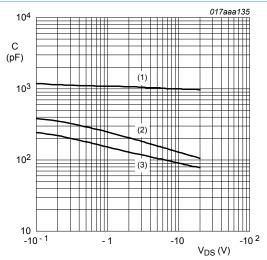
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 $I_D$  = -0.25 mA;  $V_{DS}$  =  $V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

- (1) C<sub>iss</sub>
- (2) C<sub>oss</sub>
- (3)  $C_{rss}$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

#### 20 V, P-channel Trench MOSFET

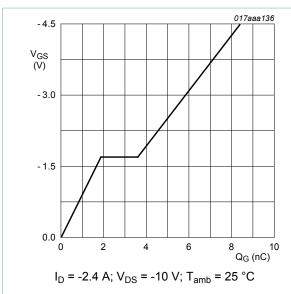


Fig. 14. Gate-source voltage as a function of gate charge; typical values

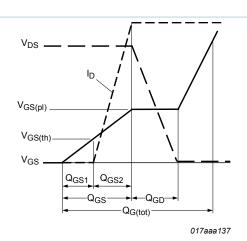
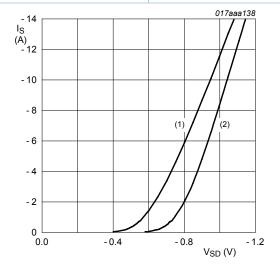


Fig. 15. Gate charge waveform definitions



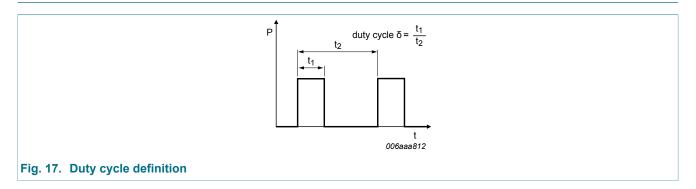
 $V_{GS} = 0 V$ (1)  $T_j = 150 \,^{\circ}C$ 

(2)  $T_i = 25 \, ^{\circ}C$ 

Fig. 16. Source current as a function of source-drain voltage; typical values

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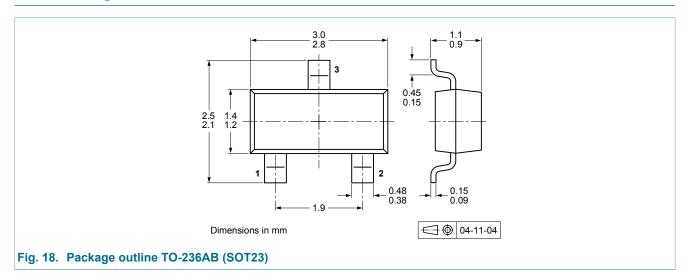
## 11. Test information



## 11.1 Quality information

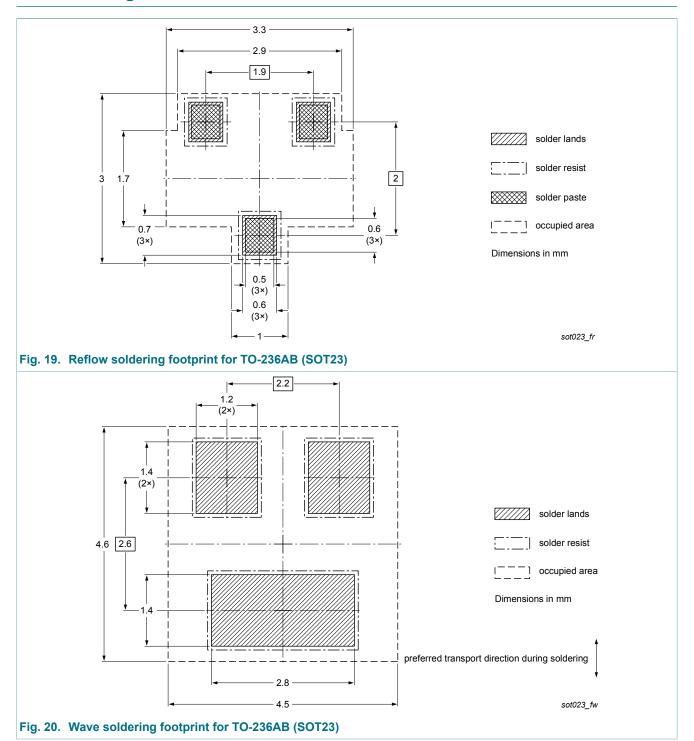
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

## 12. Package outline



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## 13. Soldering



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# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV48XPA v.1	20140310	Product data sheet	-	-

#### 20 V, P-channel Trench MOSFET

## 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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